Amendments to the Claims

Claim 1 (Previously cancelled).

D1 Claim 2 (Currently amended): A method of forming a metal-comprising mass for a semiconductor construction, comprising:

providing a semiconductor substrate;

providing one or more metallo-organic precursors proximate the substrate, at least one of the one or more precursors not comprising platinum;

exposing the one or more precursors to a reducing atmosphere to release metal from the one or more precursors;

depositing the released metal over the semiconductor substrate to form a metal-comprising mass on the semiconductor substrate; wherein the substrate comprises an upper surface consisting of one or more of TiN, elemental Ti, WN, elemental W, TaN and elemental Ta; and the upper surface is exposed to the reducing atmosphere during formation of the metal-comprising mass; and

patterning the ~~metal-containing~~ metal-comprising mass into a rectangular block.

Claim 3 (Previously cancelled)

Claim 4 (Previously amended): The method of claim 2 wherein the metal-comprising mass is formed physically against the upper surface of the substrate.

Claims 5-12 (Previously cancelled)

Claim 13 (Previously amended): The method of claim 2 wherein the reducing atmosphere comprises plasma-activated hydrogen.

Claim 14 (Previously amended): The method of claim 2 wherein the reducing atmosphere comprises H_2.

D1 cont.

Claims 15-41 (Previously cancelled)

Claim 42 (Previously added): The method of claim 2 wherein the upper surface consists of TiN.

Claim 43 (Previously added): The method of claim 2 wherein the upper surface consists of elemental Ti.

Claim 44 (Previously added): The method of claim 2 wherein the upper surface consists of WN.

Claim 45 (Previously added): The method of claim 2 wherein the upper surface consists of elemental W.

Claim 46 (Previously added): The method of claim 2 wherein the upper surface consists of TaN.

D1

Claim 47 (Previously added): The method of claim 2 wherein the upper surface consists of elemental Ta.
